



# Advanced CMOS Logic – 54AC14

## Hex Schmitt-Trigger Inverter Logic IC in bare die form

Rev 2.0  
12/03/26

### Description

The 54AC14 Hex Schmitt-Trigger Inverter is fabricated using a 5V CMOS process with the same high speed performance of LSTTL combined with CMOS low power consumption. The device performs the Boolean function  $Y = \bar{A}$  in positive logic. Device inputs are compatible with Standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs. Schmitt-Trigger inputs transform slow input rise and fall times into sharply defined jitter-free output signals. Due to the hysteresis voltage of the Schmitt trigger, the 54AC14 is useful in noisy environments.

### Features:

- Outputs Sink/Source 24mA
- Low Input Current: 1µA
- Outputs directly interface CMOS, NMOS and TTL
- Operating Voltage Range: 2V to 6V
- CMOS High Noise Immunity
- Function compatible with 54HC14 or 54LS14
- Full Military Temperature Range.

### Ordering Information

The following part suffixes apply:

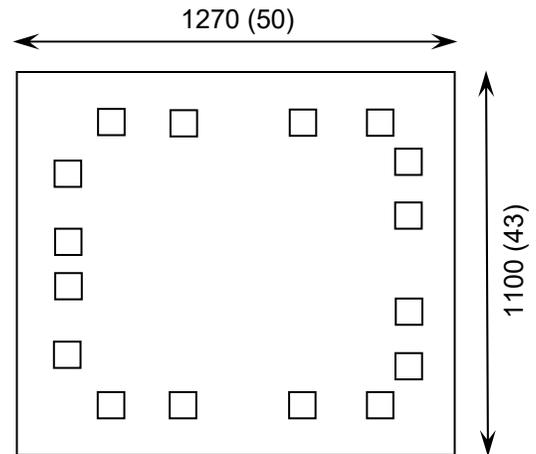
- No suffix - MIL-STD-883 /2010B Visual Inspection
- "H" - MIL-STD-883 /2010B Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" - MIL-STD-883 /2010A Visual Inspection (Space) + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

[www.siliconsupplies.com/quality/bare-die-lot-qualification](http://www.siliconsupplies.com/quality/bare-die-lot-qualification)

### Die Dimensions in µm (mils)



### Supply Formats:

- Default – Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape – On request
- Unsawn Wafer – On request
- Die Thickness <=> 280µm(11 Mils) – On request
- Assembled into Ceramic Package – On request

### Mechanical Specification

Die Size (Unsawn)	1270 x 1100 50 x 43	µm mils
Minimum Bond Pad Size	70 x 70 2.76 x 2.76	µm mils
Die Thickness	280 (±20) 11.02 (±0.79)	µm mils
Top Metal Composition	Al-Si-Cu	
Back Metal Composition	N/A – Bare Si	

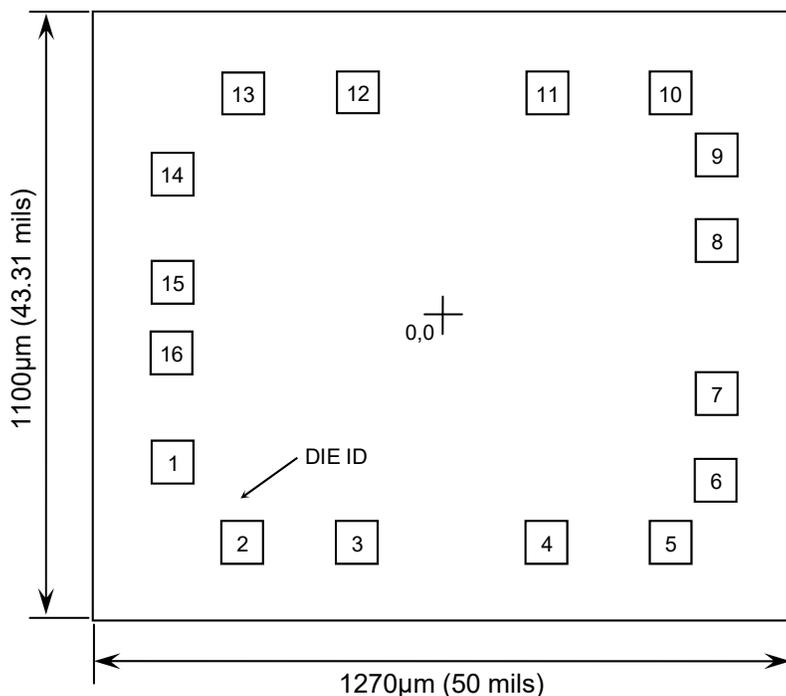




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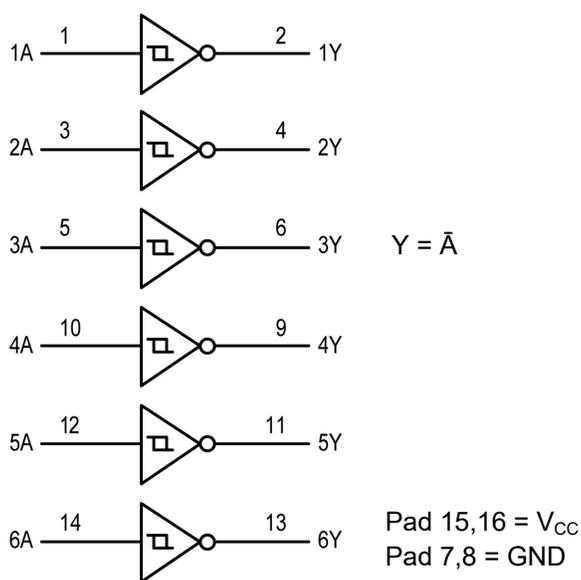
## Pad Layout and Functions



PAD	FUNCTION	COORDINATES (µm)	
		X	Y
1	1A	-502	-263.5
2	1Y	-364.9	-410
3	2A	-157.7	-410
4	2Y	188.9	-410
5	3A	413	-410
6	3Y	495	-298
7	GND	495	-140
8	GND	495	140
9	4Y	495	298
10	4A	413	410
11	5Y	188.9	410
12	5A	-157.7	410
13	6Y	-364.9	410
14	6A	-495	263
15	V <sub>CC</sub>	-495	64.2
16	V <sub>CC</sub>	-495	-64.2

CHIP BACK IS ISOLATED

## Logic Diagram



## Function Table

INPUTS	OUTPUT
A	Y
H	L
L	H

H = High level (steady state)  
L = Low level (steady state)





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## Absolute Maximum Ratings<sup>1</sup>

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	$V_{CC}$	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	$V_{IN}$	-0.5 to $V_{CC} + 0.5$	V
DC Output Voltage (Referenced to GND)	$V_{OUT}$	-0.5 to $V_{CC} + 0.5$	V
DC Input Current	$I_{IN}$	$\pm 20$	mA
DC Output Current, per pad	$I_{OUT}$	$\pm 50$	mA
DC Supply Current, $V_{CC}$ or GND, per pad	$I_{CC}$	$\pm 50$	mA
Power Dissipation in Still Air <sup>2</sup>	$P_D$	750	mW
Storage Temperature Range	$T_{STG}$	-65 to 150	$^{\circ}C$

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

## Recommended Operating Conditions<sup>3</sup> (Voltages referenced to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS	
DC Supply Voltage	$V_{CC}$	2	6	V	
DC Input or Output Voltage	$V_{IN}, V_{OUT}$	0	$V_{CC}$	V	
Operating Temperature Range	$T_J$	-55	+125	$^{\circ}C$	
Output Current – High	$I_{OH}$	-	-24	mA	
Output Current – Low	$I_{OL}$	-	24	mA	
Input Rise and Fall Time (Except Schmitt Inputs), $V_{IN}$ from 30% to 70% $V_{CC}$	$V_{CC} = 3.0V$	$t_r, t_f$	0	150	ns/V
	$V_{CC} = 4.5V$		0	40	
	$V_{CC} = 5.5V$		0	24	

3. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{IN}$  and  $V_{OUT}$  should be constrained to the range  $GND \leq (V_{IN} \text{ or } V_{OUT}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

## DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	$V_{CC}$	CONDITIONS	LIMITS			UNITS
				25 $^{\circ}C$	85 $^{\circ}C$	FULL RANGE <sup>4</sup>	
Maximum Positive Threshold	$V_{T+}$	3.0V	$V_{OUT} = 0.1V$	2.2	2.2	2.2	V
		4.5V		3.2	3.2	3.2	
		5.5V		3.9	3.9	3.9	
Minimum Negative Threshold	$V_{T-}$	3.0V	$V_{OUT} = 0.1V$	0.5	0.5	0.5	V
		4.5V		0.9	0.9	0.9	
		5.5V		1.1	1.1	1.1	

4.  $-55^{\circ}C \leq T_J \leq +125^{\circ}C$





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## DC Electrical Characteristics Continued (Voltages Referenced to GND)

PARAMETER	SYMBOL	V <sub>CC</sub>	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE <sup>4</sup>	
Maximum Hysteresis Voltage <sup>5</sup>	V <sub>H MAX</sub>	3.0V	V <sub>OUT</sub> = 0.1V or V <sub>CC</sub> -0.1V	1.2	1.2	1.2	V
		4.5V		1.4	1.4	1.4	V
		5.5V		1.6	1.6	1.6	V
Minimum Hysteresis Voltage <sup>5</sup>	V <sub>H MIN</sub>	3.0V	V <sub>OUT</sub> = 0.1V or V <sub>CC</sub> -0.1V	0.3	0.3	0.3	V
		4.5V		0.4	0.4	0.4	V
		5.5V		0.5	0.5	0.5	V
Minimum High-Level Output Voltage	V <sub>OH</sub>	3.0V	I <sub>OUT</sub> ≤ -50μA	2.9	2.9	2.9	V
		4.5V		4.4	4.4	4.4	
		5.5V		5.4	5.4	5.4	
	3.0V	V <sub>IN</sub> ≤ V <sub>T-</sub> min, I <sub>OH</sub> = -12mA <sup>6</sup>	2.56	2.46	2.40		
	4.5V	V <sub>IN</sub> ≤ V <sub>T-</sub> min, I <sub>OH</sub> = -24mA <sup>6</sup>	3.86	3.76	3.70		
	5.5V	V <sub>IN</sub> ≤ V <sub>T-</sub> min, I <sub>OH</sub> = -24mA <sup>6</sup>	4.86	4.76	4.70		
	5.5V	V <sub>IN</sub> ≤ V <sub>T-</sub> min, I <sub>OH</sub> = -50mA <sup>7</sup>	-	-	3.85		
Maximum Low-Level Output Voltage	V <sub>OL</sub>	3.0V	I <sub>OUT</sub> ≤ 50μA	0.1	0.1	0.1	V
		4.5V		0.1	0.1	0.1	
		5.5V		0.1	0.1	0.1	
	3.0V	V <sub>IN</sub> ≥ V <sub>T-</sub> min, I <sub>OL</sub> = 12mA <sup>6</sup>	0.36	0.44	0.5		
	4.5V	V <sub>IN</sub> ≥ V <sub>T-</sub> min, I <sub>OL</sub> = 24mA <sup>6</sup>	0.36	0.44	0.5		
	5.5V	V <sub>IN</sub> ≥ V <sub>T-</sub> min, I <sub>OL</sub> = 24mA <sup>6</sup>	0.36	0.44	0.5		
	5.5V	V <sub>IN</sub> ≥ V <sub>T-</sub> min, I <sub>OL</sub> = 50mA <sup>7</sup>	-	-	1.65		
Maximum Input Leakage Current	I <sub>IN</sub>	5.5V	V <sub>IN</sub> = V <sub>CC</sub> or GND	±0.1	±1.0	±1.0	μA
Minimum Dynamic Output Current <sup>8</sup>	I <sub>OLD</sub>	5.5V	V <sub>OLD</sub> = 1.65V Max	-	75	50	mA
	I <sub>OHD</sub>	5.5V	V <sub>OHD</sub> = 3.85V Min	-	-75	-50	
Maximum Quiescent Supply Current	I <sub>CC</sub>	5.5V	V <sub>IN</sub> = V <sub>CC</sub> or GND	4	40	80	μA

5. V<sub>H</sub> = (V<sub>T+</sub>) - (V<sub>T-</sub>) 6. All outputs loaded; thresholds on input associated with output under test. 7. Test time 1sec max, measurement made by forcing indicated current and measuring voltage to minimize power dissipation. Test verifies a minimum 75Ω transmission-line drive capability at 125°C 8. Maximum test duration 2ms, one output loaded at a time.





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## AC Electrical Characteristics<sup>9</sup>

PARAMETER	SYMBOL	V <sub>CC</sub> <sup>10</sup>	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE <sup>4</sup>	
Maximum Propagation Delay, Input A or B to Output Y (Figure 1,2)	t <sub>PLH</sub>	3.3V	C <sub>L</sub> = 50pF, Input t <sub>r</sub> =t <sub>f</sub> = 3ns	13.5	15.0	16.0	ns
		5.0V		10.0	11.0	12.0	
	t <sub>PHL</sub>	3.3V	C <sub>L</sub> = 50pF, Input t <sub>r</sub> =t <sub>f</sub> = 3ns	11.5	13.0	14.0	ns
		5.0V		8.5	9.5	10.0	
Maximum Input Capacitance	C <sub>IN</sub>	5	-	4.5	4.5	4.5	pF
Power Dissipation Capacitance Per Gate <sup>11</sup>	C <sub>PD</sub>	-	T <sub>A</sub> = 25°C, V <sub>CC</sub> = 5.0V	TYPICAL			pF
				25			

9. Not production tested in die form, characterized by chip design and tested in package. 10. ± 10% 11. Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

## Switching Waveform

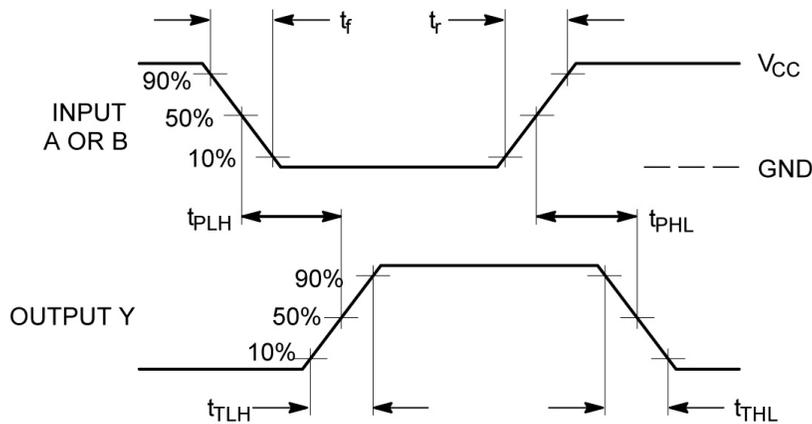
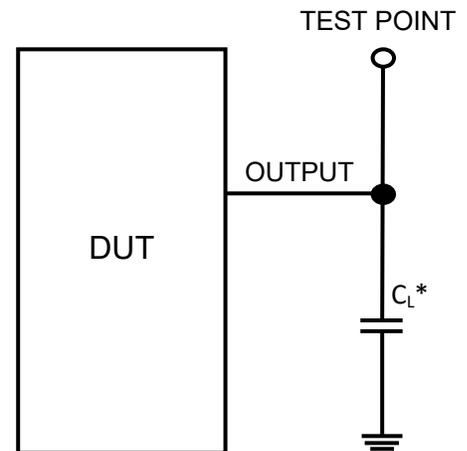


Figure 1 – Propagation Delay & Output Transition Time

## Test Circuit



\* Includes all probe and jig capacitance

Figure 2

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